crystalline semiconductor film,

wherein the first laser beam has a wavelength of 308 nm, and

wherein the second laser beam has a wavelength of 532 nm.

15 (New). A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film; and

irradiating the first crystalline semiconductor film with a second laser beam to from a second crystalline semiconductor film,

wherein the first laser beam is an excimer laser beam, and

wherein the second laser beam has a wavelength of 532 nm.

16 (New). A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film; and

irradiating the first crystalline semiconductor film with a second laser beam to from a second crystalline semiconductor film,

wherein the first laser beam is an excimer laser beam, and

wherein the second laser beam has a wavelength of 370 to 650 nm.

17 (New). A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film; and

irradiating the first crystalline semiconductor film with a second laser beam to from a second crystalline semiconductor film,

wherein the first laser beam has a wavelength of 126 to 370 nm, and

wherein the second laser beam has a wavelength of 532 nm.

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18 (New). A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a second laser beam to from a second crystalline semiconductor film;

patterning the second crystalline semiconductor film into a crystalline semiconductor island; and

forming a source region and a drain region in the crystalline semiconductor island by introducing an impurity thereinto with a channel region between the source region and the drain region,

wherein the first laser beam has a wavelength of 308 nm, and

wherein the second laser beam has a wavelength of 532 nm.

19 (New). A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a second laser beam to from a second crystalline semiconductor film;

patterning the second crystalline semiconductor film into a crystalline semiconductor island; and

forming a source region and a drain region in the crystalline semiconductor island by introducing an impurity thereinto with a channel region between the source region and the drain region,

wherein the first laser beam is an excimer laser beam, and

wherein the second laser beam has a wavelength of 532 nm.

20 (New). A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a second laser beam to from a second crystalline semiconductor film,

patterning the second crystalline semiconductor film into a crystalline semiconductor island; and

forming a source region and a drain region in the crystalline semiconductor island by introducing an impurity thereinto with a channel region between the source region and the drain region,

wherein the first laser beam is an excimer laser beam, and

wherein the second laser beam has a wavelength of 370 to 650 nm.

21 (New). A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a second laser beam to from a second crystalline semiconductor film,

patterning the second crystalline semiconductor film into a crystalline semiconductor island; and

forming a source region and a drain region in the crystalline semiconductor island by introducing an impurity thereinto with a channel region between the source region and the drain region,

wherein the first laser beam has a wavelength of 126 to 370 nm, and

wherein the second laser beam has a wavelength of 532 nm.

22 (New). A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a second laser beam to from a second crystalline semiconductor film,

patterning the second crystalline semiconductor film into a crystalline semiconductor island; and

forming a source region and a drain region in the crystalline semiconductor island by introducing an impurity thereinto with a channel region between the source region and the drain region,

wherein the first laser beam is 126 to 370 nm in wavelength, and

wherein the second laser beam is 370 to 650 nm in wavelength.

23 (New). A method according to claim 14 wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

24 (New). A method according to claim 14 wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display and a light emitting device.

25 (New). A method according to claim 15 wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a

digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

26 (New). A method according to claim 15 wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display and a light emitting device.

27 (New). A method according to claim 16 wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

28 (New). A method according to claim 16 wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display and a light emitting device.

29 (New). A method according to claim 17 wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

30 (New). A method according to claim 17 wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display and a light emitting device.

31 (New). A method according to claim 18 wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

32 (New). A method according to claim 18 wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display and a light emitting device.

33 (New). A method according to claim 19 wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

34 (New). A method according to claim 19 wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display and a light emitting device.

35 (New). A method according to claim 20 wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

36 (new). A method according to claim 20 wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display and a light emitting device.

37 (New). A method according to claim 21 wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

38 (New). A method according to claim 21 wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display and a light emitting device.

39 (New). A method according to claim 22 wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

40 (New). A method according to claim 22 wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display and a light emitting device.

## REMARKS

Applicant is submitting a RCE herewith in order to enter the new claims and IDS also submitted herewith.

New Claims

The fee for new claims has been calculated as shown below.

| | Claims Remaining After Amendment | | Highest Number Previously Paid For | Present Extra | Rate | Fee |
|---|---|---|---|---|---|---|
| Total | 40 | - | 20 | 20 | (small entity) x 9<br>(others) x 18 | $360.00 |
| Independent | 13 | - | 4 | 9 | (small entity) x 42<br>(others) x 84 | $756.00 |
| Multiple Dependent (None) | | | | | (small entity) + 140<br>(others) + 280 | $0.00 |
| TOTAL ADDITIONAL FEES | | | | | | $ 1116.00 |

Applicant is enclosing the $1116.00 fee for the new claims and new independent claims.

IDS

Applicant is submitting a new IDS herewith and request consideration of it.